Description

The M16C/62M group of single-chip microcomputers are built using the high-performance silicon gate CMOS process using a M16C/60 Series CPU core and are packaged in a 100-pin plastic molded QFP. These single-chip microcomputers operate using sophisticated instructions featuring a high level of instruction efficiency. With 1M bytes of address space, low voltage (2.2V to 3.6V), they are capable of executing instructions at high speed. They also feature a built-in multiplier and DMAC, making them ideal for controlling office, communications, industrial equipment, and other high-speed processing applications.

The M16C/62M group includes a wide range of products with different internal memory types and sizes and various package types.

Features

- Memory capacity ..... ROM (See Figure 1.1.4. ROM Expansion)
  RAM 10K to 20K bytes
- Shortest instruction execution time ..... 100ns (f(X_{IN})=10MHz, V_{CC}=2.7V to 3.6V)
  142.9ns (f(X_{IN})=7MHz, V_{CC}=2.2V to 3.6V with software one-wait)
- Supply voltage ..... 2.7V to 3.6V (f(X_{IN})=10MHz, without software wait)
  2.4V to 2.7V (f(X_{IN})=7MHz, without software wait)
  2.2V to 2.4V (f(X_{IN})=7MHz with software one-wait)
- Low power consumption ..... 28.5mW (V_{CC} = 3V, f(X_{IN})=10MHz, without software wait)
- Interrupts ..... 25 internal and 8 external interrupt sources, 4 software interrupt sources; 7 levels (including key input interrupt)
- Multifunction 16-bit timer ..... 5 output timers + 6 input timers
- Serial I/O ..... 5 channels
  (3 for UART or clock synchronous, 2 for clock synchronous)
- DMAC ..... 2 channels (trigger: 24 sources)
- A-D converter ..... 10 bits X 8 channels (Expandable up to 10 channels)
- D-A converter ..... 8 bits X 2 channels
- CRC calculation circuit ..... 1 circuit
- Watchdog timer ..... 1 line
- Programmable I/O ..... 87 lines
- Input port ..... 1 line ($P8_5$ shared with $\overline{NMI}$ pin)
- Memory expansion ..... Available (to a maximum of 1M bytes)
- Chip select output ..... 4 lines
- Clock generating circuit ..... 2 built-in clock generation circuits
  (built-in feedback resistor, and external ceramic or quartz oscillator)

Applications

Audio, cameras, office equipment, communications equipment, portable equipment

Pin Configuration

Figures 1.1.1 and 1.1.2 show the pin configurations (top view).

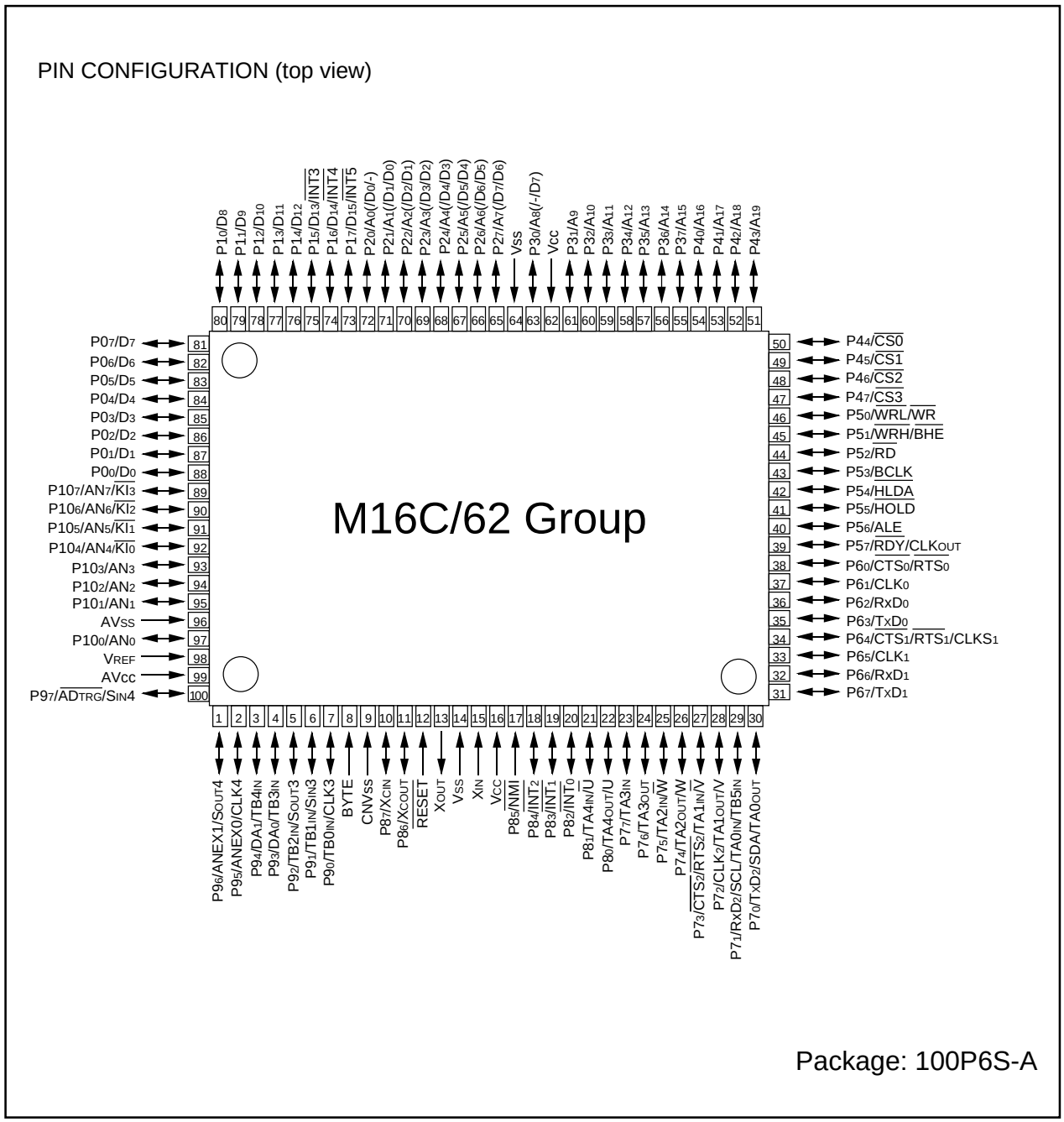


Figure 1.1.1. Pin configuration (top view)

PIN CONFIGURATION (top view)

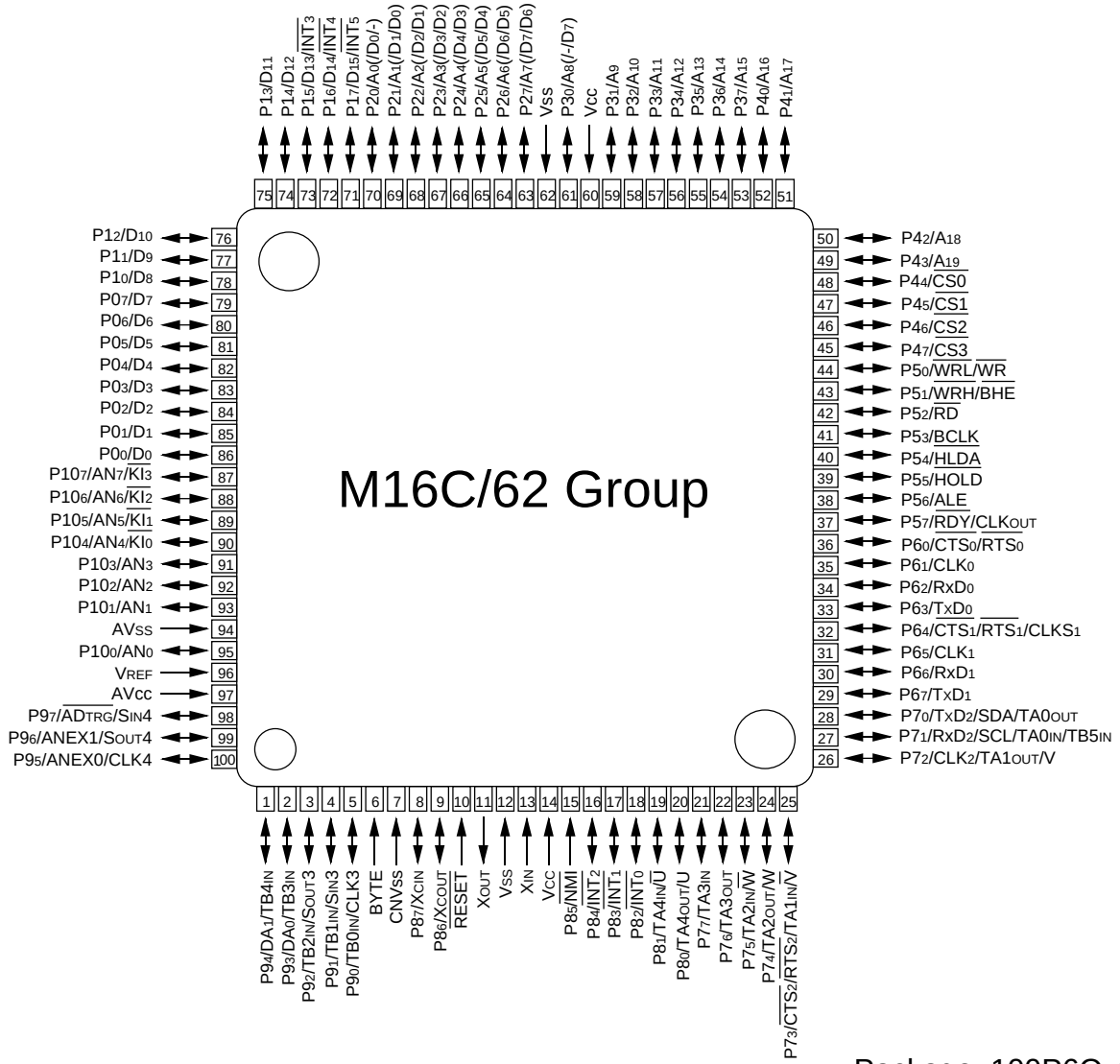
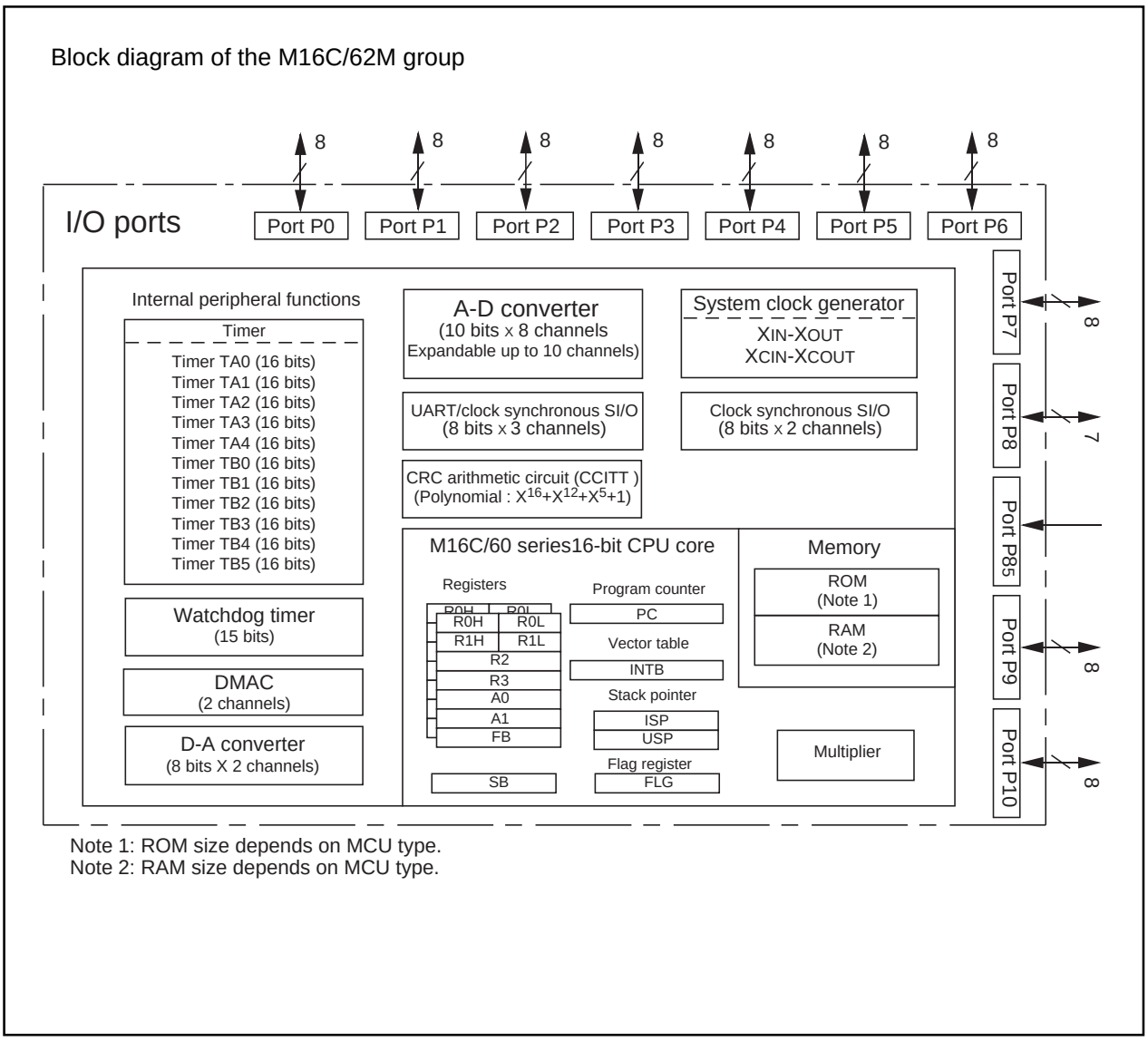


Figure 1.1.2. Pin configuration (top view)

Block Diagram

Figure 1.1.3 is a block diagram of the M16C/62M group.



Note 1: ROM size depends on MCU type.
Note 2: RAM size depends on MCU type.

Figure 1.1.3. Block diagram of M16C/62M group

Performance Outline

Table 1.1.1 is a performance outline of M16C/62M group.

Table 1.1.1. Performance outline of M16C/62M group

Item		Performance
Number of basic instructions		91 instructions
Shortest instruction execution time		100ns(f(XIN)=10MHz, VCC=2.7V to 3.6V) 142.9ns (f(XIN)=7MHz, VCC=2.2V to 3.6V with software one-wait)
Memory capacity	ROM	(See the figure 1.1.4. ROM Expansion)
	RAM	10K to 20K bytes
I/O port	P0 to P10 (except P85)	8 bits x 10, 7 bits x 1
Input port	P85	1 bit x 1
Multifunction timer	TA0, TA1, TA2, TA3, TA4	16 bits x 5
	TB0, TB1, TB2, TB3, TB4, TB5	16 bits x 6
Serial I/O	UART0, UART1, UART2	(UART or clock synchronous) x 3
	SI/O3, SI/O4	(Clock synchronous) x 2
A-D converter		10 bits x (8 + 2) channels
D-A converter		8 bits x 2
DMAC		2 channels (trigger: 24 sources)
CRC calculation circuit		CRC-CCITT
Watchdog timer		15 bits x 1 (with prescaler)
Interrupt		25 internal and 8 external sources, 4 software sources, 7 levels
Clock generating circuit		2 built-in clock generation circuits (built-in feedback resistor, and external ceramic or quartz oscillator)
Supply voltage		2.7V to 3.6V (f(XIN)=10MHz, without software wait) 2.4V to 2.7V (f(XIN)=7MHz, without software wait) 2.2V to 2.4V (f(XIN)=7MHz with software one-wait)
Power consumption		28.5mW (f(XIN) =10MHz, VCC=3V without software wait)
I/O characteristics	I/O withstand voltage	3V
	Output current	1mA
Memory expansion		Available (to a maximum of 1M bytes)
Device configuration		CMOS high performance silicon gate
Package		100-pin plastic mold QFP

Mitsubishi plans to release the following products in the M16C/62M group:

(1) Support for mask ROM version and Flash memory version

(2) ROM capacity

(3) Package

100P6S-A : Plastic molded QFP (mask ROM and flash memory versions)

100P6Q-A : Plastic molded QFP (mask ROM and flash memory versions)

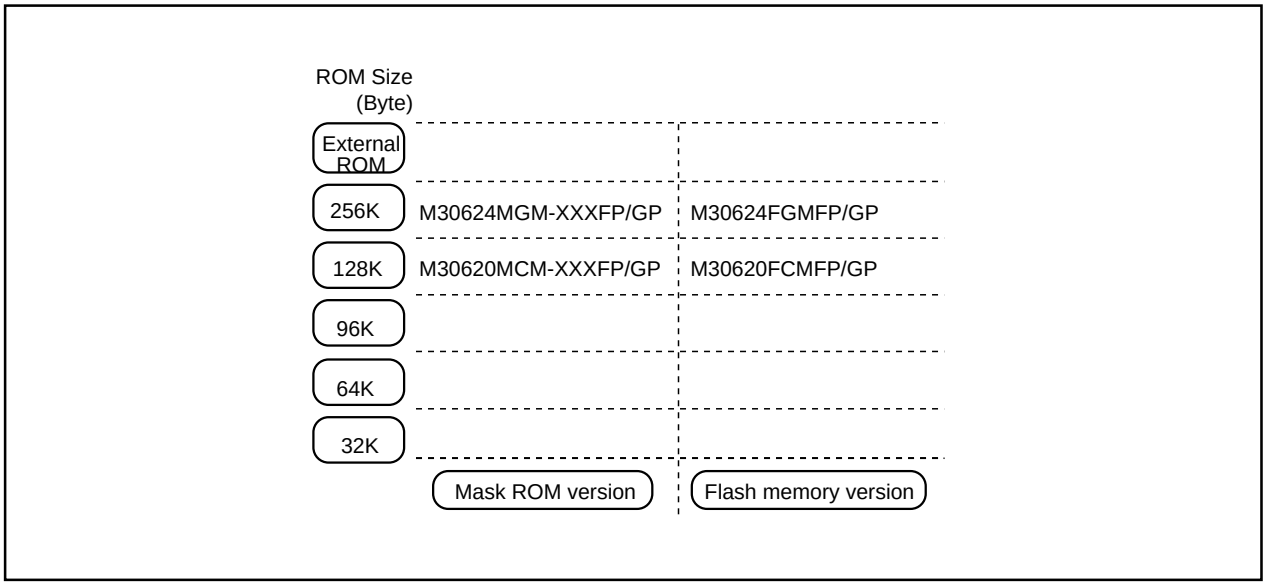


Figure 1.1.4. ROM expansion

The M16C/62M group products currently supported are listed in Table 1.1.2.

Table 1.1.2. M16C/62M group

June, 2000

Type No	ROM capacity	RAM capacity	Package type	Remarks
M30620MCM-XXXFP	128K byte	10K byte	100P6S-A	mask ROM version
M30620MCM-XXXGP			100P6Q-A	
M30624MGM-XXXFP	256K byte	20K byte	100P6S-A	
M30624MGM-XXXGP			100P6Q-A	
M30620FCMFP	128K byte	10K byte	100P6S-A	Flash memory 3V version
M30620FCMGP			100P6Q-A	
M30624FGMFP	256K byte	20K byte	100P6S-A	
M30624FGMGP			100P6Q-A	

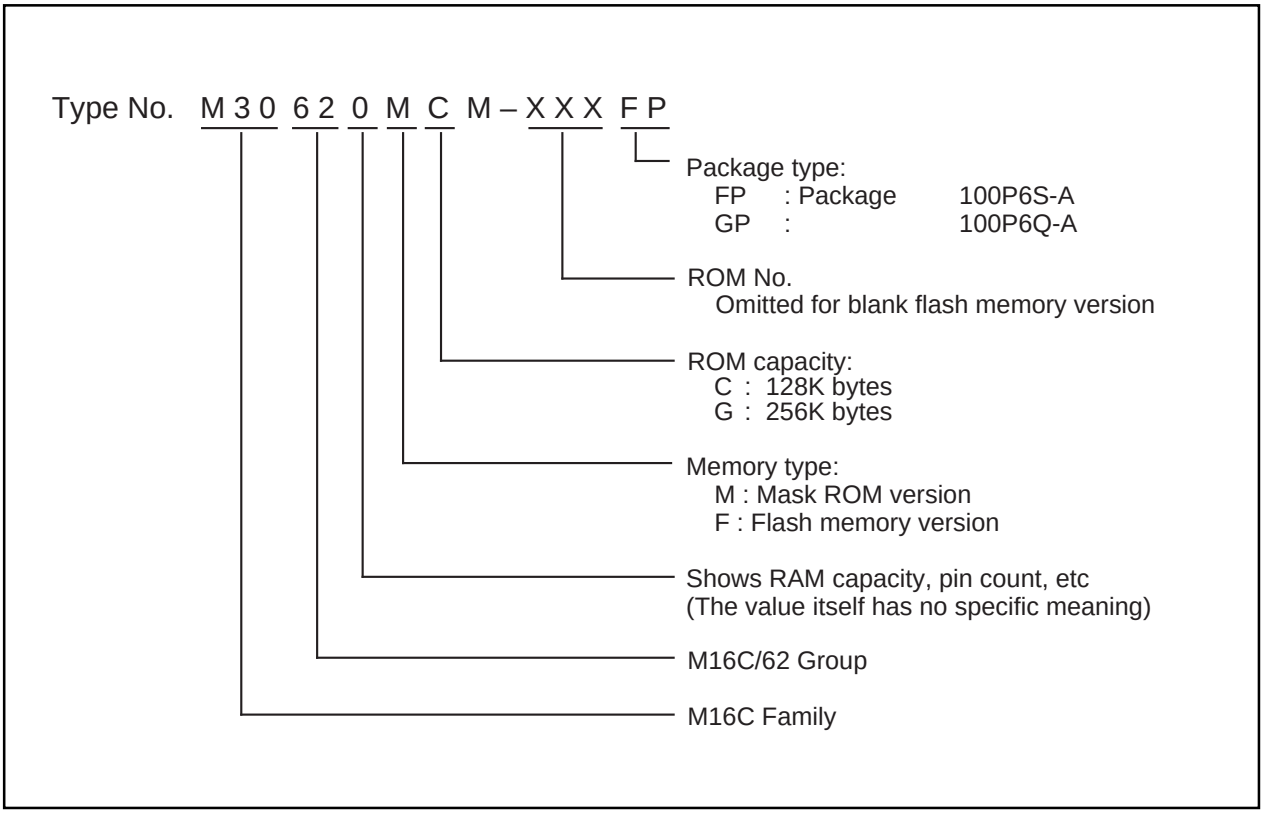


Figure 1.1.5. Type No., memory size, and package

Table 1.26.1. Absolute maximum ratings

Symbol	Parameter		Condition	Rated value	Unit
Vcc	Supply voltage		Vcc=AVcc	- 0.3 to 4.6	V
AVcc	Analog supply voltage		Vcc=AVcc	- 0.3 to 4.6	V
V_I	Input voltage	$\overline{RESET}$, CNV$_{SS}$, BYTE, P0$_0$ to P0$_7$, P1$_0$ to P1$_7$, P2$_0$ to P2$_7$, P3$_0$ to P3$_7$,P4$_0$ to P4$_7$, P5$_0$ to P5$_7$, P6$_0$ to P6$_7$, P7$_2$ to P7$_7$, P8$_0$ to P8$_7$, P9$_0$ to P9$_7$, P10$_0$ to P10$_7$, V_{REF}, X_{IN}		- 0.3 to Vcc + 0.3	V
		P7$_0$, P7$_1$		- 0.3 to 4.6	V
V_O	Output voltage	P0$_0$ to P0$_7$, P1$_0$ to P1$_7$, P2$_0$ to P2$_7$, P3$_0$ to P3$_7$, P4$_0$ to P4$_7$, P5$_0$ to P5$_7$, P6$_0$ to P6$_7$, P7$_2$ to P7$_7$, P8$_0$ to P8$_4$, P8$_6$, P8$_7$, P9$_0$ to P9$_7$, P10$_0$ to P10$_7$, X_{OUT}		- 0.3 to Vcc + 0.3	V
		P7$_0$, P7$_1$		- 0.3 to 4.6	V
P_d	Power dissipation		Ta=25 °C	300	mW
T_{opr}	Operating ambient temperature			- 20 to 85 / -40 to 85 (Note)	°C
T_{stg}	Storage temperature			- 65 to 150	°C

Note : Specify a product of -40°C to 85°C to use it.

Table 1.26.2. Recommended operating conditions (referenced to V_{CC} = 2.2V to 3.6V at Ta = – 20°C to 85°C / – 40°C to 85°C(Note3) unless otherwise specified)

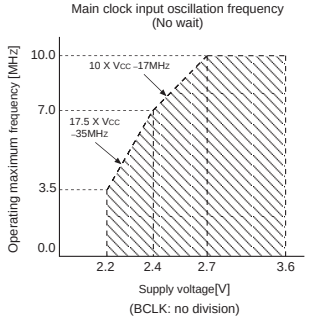
Symbol	Parameter			Standard			Unit
				Min.	Typ.	Max.	
Vcc	Supply voltage			2.2	3.0	3.6	V
AVcc	Analog supply voltage				Vcc		V
Vss	Supply voltage				0		V
AVss	Analog supply voltage				0		V
V_{IH}	HIGH input voltage	$P3_1$ to $P3_7$, $P4_0$ to $P4_7$, $P5_0$ to $P5_7$, $P6_0$ to $P6_7$, $P7_2$ to $P7_7$, $P8_0$ to $P8_7$, $P9_0$ to $P9_7$, $P10_0$ to $P10_7$, X_{IN}, RESET, CNV_{SS}, BYTE		0.8Vcc		Vcc	V
		$P7_0$, $P7_1$		0.8Vcc		4.6	V
		$P0_0$ to $P0_7$, $P1_0$ to $P1_7$, $P2_0$ to $P2_7$, $P3_0$ (during single-chip mode)		0.8Vcc		Vcc	V
		$P0_0$ to $P0_7$, $P1_0$ to $P1_7$, $P2_0$ to $P2_7$, $P3_0$ (data input function during memory expansion and microprocessor modes)		0.5Vcc		Vcc	V
V_{IL}	LOW input voltage	$P3_1$ to $P3_7$, $P4_0$ to $P4_7$, $P5_0$ to $P5_7$, $P6_0$ to $P6_7$, $P7_0$ to $P7_7$, $P8_0$ to $P8_7$, $P9_0$ to $P9_7$, $P10_0$ to $P10_7$, X_{IN}, RESET, CNV_{SS}, BYTE		0		0.2Vcc	V
		$P0_0$ to $P0_7$, $P1_0$ to $P1_7$, $P2_0$ to $P2_7$, $P3_0$ (during single-chip mode)		0		0.2Vcc	V
		$P0_0$ to $P0_7$, $P1_0$ to $P1_7$, $P2_0$ to $P2_7$, $P3_0$ (data input function during memory expansion and microprocessor modes)		0		0.16Vcc	V
$I_{OH (peak)}$	HIGH peak output current	$P0_0$ to $P0_7$, $P1_0$ to $P1_7$, $P2_0$ to $P2_7$, $P3_0$ to $P3_7$, $P4_0$ to $P4_7$, $P5_0$ to $P5_7$, $P6_0$ to $P6_7$, $P7_2$ to $P7_7$, $P8_0$ to $P8_4$, $P8_6$, $P8_7$, $P9_0$ to $P9_7$, $P10_0$ to $P10_7$				- 10.0	mA
$I_{OH (avg)}$	HIGH average output current	$P0_0$ to $P0_7$, $P1_0$ to $P1_7$, $P2_0$ to $P2_7$, $P3_0$ to $P3_7$, $P4_0$ to $P4_7$, $P5_0$ to $P5_7$, $P6_0$ to $P6_7$, $P7_2$ to $P7_7$, $P8_0$ to $P8_4$, $P8_6$, $P8_7$, $P9_0$ to $P9_7$, $P10_0$ to $P10_7$				- 5.0	mA
$I_{OL (peak)}$	LOW peak output current	$P0_0$ to $P0_7$, $P1_0$ to $P1_7$, $P2_0$ to $P2_7$, $P3_0$ to $P3_7$, $P4_0$ to $P4_7$, $P5_0$ to $P5_7$, $P6_0$ to $P6_7$, $P7_0$ to $P7_7$, $P8_0$ to $P8_4$, $P8_6$, $P8_7$, $P9_0$ to $P9_7$, $P10_0$ to $P10_7$				10.0	mA
$I_{OL (avg)}$	LOW average output current	$P0_0$ to $P0_7$, $P1_0$ to $P1_7$, $P2_0$ to $P2_7$, $P3_0$ to $P3_7$, $P4_0$ to $P4_7$, $P5_0$ to $P5_7$, $P6_0$ to $P6_7$, $P7_0$ to $P7_7$, $P8_0$ to $P8_4$, $P8_6$, $P8_7$, $P9_0$ to $P9_7$, $P10_0$ to $P10_7$				5.0	mA
f (X_{IN})	Main clock input oscillation frequency	No wait	Vcc=2.7V to 3.6V	0		10	MHz
			Vcc=2.4V to 2.7V	0		10 X Vcc - 17	MHz
			Vcc=2.2V to 2.4V	0		17.5 X Vcc - 35	MHz
		with wait	Vcc=2.7V to 3.6V	0		10	MHz
			Vcc=2.2V to 2.7V	0		6 X Vcc - 6.2	MHz
f (X_{CIN})	Subclock oscillation frequency				32.768	50	kHz

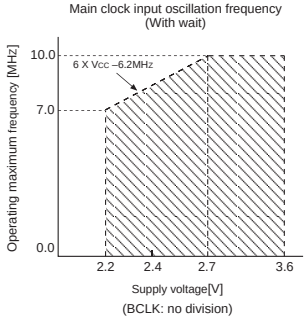
Note 1: The mean output current is the mean value within 100ms.

Note 2: The total I_{OL} (peak) for ports P0, P1, P2, $P8_6$, $P8_7$, P9, and P10 must be 80mA max. The total I_{OH} (peak) for ports P0, P1, P2, $P8_6$, $P8_7$, P9, and P10 must be 80mA max. The total I_{OL} (peak) for ports P3, P4, P5, P6, P7, and $P8_0$ to $P8_4$ must be 80mA max. The total I_{OH} (peak) for ports P3, P4, P5, P6, $P7_2$ to $P7_7$, and $P8_0$ to $P8_4$ must be 80mA max.

Note 3: Specify a product of -40°C to 85°C to use it.

Note 4: Relationship between main clock oscillation frequency and supply voltage.





Flash memory version program voltage and read operation voltage characteristics

Flash program voltage	Flash read operation voltage
Vcc=2.7V to 3.6V	Vcc=2.4V to 3.6V
Vcc=2.7V to 3.4V	Vcc=2.2V to 2.4V

Note 5: Execute case without wait, program / erase of flash memory by Vcc=2.7V to 3.6V and f(BCLK) ≤ 6.25 MHz. Execute case with wait, program / erase of flash memory by Vcc=2.7V to 3.6V and f(BCLK) ≤ 10.0 MHz.

Table 1.26.3. Electrical characteristics (referenced to V_{CC} = 2.7V to 3.6V, V_{SS} = 0V at Ta = – 20°C to 85°C / – 40°C to 85°C (Note1), f(X_{IN}) = 10MHz without wait unless otherwise specified)

Symbol	Parameter			Measuring condition		Standard Min	Standard Typ.	Standard Max.	Unit
V_{OH}	HIGH output voltage	$P0_0$ to $P0_7$, $P1_0$ to $P1_7$, $P2_0$ to $P2_7$, $P3_0$ to $P3_7$, $P4_0$ to $P4_7$, $P5_0$ to $P5_7$, $P6_0$ to $P6_7$, $P7_2$ to $P7_7$, $P8_0$ to $P8_4$, $P8_6$,$P8_7$, $P9_0$ to $P9_7$, $P10_0$ to $P10_7$		I_{OH}=–1mA		2.5			V
V_{OH}	HIGH output voltage	X_{OUT}	HIGHPOWER	I_{OH}=–0.1mA		2.5			V
			LOWPOWER	I_{OH}=–50µA		2.5			
	HIGH output voltage	X_{COUT}	HIGHPOWER	With no load applied			3.0		V
			LOWPOWER	With no load applied			1.6		
V_{OL}	LOW output voltage	$P0_0$ to $P0_7$, $P1_0$ to $P1_7$, $P2_0$ to $P2_7$, $P3_0$ to $P3_7$, $P4_0$ to $P4_7$, $P5_0$ to $P5_7$, $P6_0$ to $P6_7$, $P7_0$ to $P7_7$, $P8_0$ to $P8_4$, $P8_6$,$P8_7$, $P9_0$ to $P9_7$, $P10_0$ to $P10_7$		I_{OL}=1mA				0.5	V
V_{OL}	LOW output voltage	X_{OUT}	HIGHPOWER	I_{OL}=0.1mA				0.5	V
			LOWPOWER	I_{OL}=50µA				0.5	
	LOW output voltage	X_{COUT}	HIGHPOWER	With no load applied			0		V
			LOWPOWER	With no load applied			0		
V_{T+}–V_{T-}	Hysteresis	$\overline{HOLD}$, $\overline{RDY}$, $TA0_{IN}$ to $TA4_{IN}$, $TB0_{IN}$ to $TB5_{IN}$, $\overline{INT0}$ to $\overline{INT5}$, $\overline{NMI}$, $\overline{ADTRG}$, $\overline{CTS0}$ to $\overline{CTS2}$, SCL, SDA, CLK_0 to CLK_4, $TA2_{OUT}$ to $TA4_{OUT}$, $\overline{KI0}$ to $\overline{KI3}$, RxD_0 to RxD_2, S_{IN3}, S_{IN4}				0.2		0.8	V
V_{T+}–V_{T-}	Hysteresis	$\overline{RESET}$				0.2		1.8	V
I_{IH}	HIGH input current	$P0_0$ to $P0_7$, $P1_0$ to $P1_7$, $P2_0$ to $P2_7$, $P3_0$ to $P3_7$, $P4_0$ to $P4_7$, $P5_0$ to $P5_7$, $P6_0$ to $P6_7$, $P7_0$ to $P7_7$, $P8_0$ to $P8_7$, $P9_0$ to $P9_7$, $P10_0$ to $P10_7$, X_{IN}, $\overline{RESET}$, CNVss, BYTE		V_I=3V				4.0	µA
I_{IL}	LOW input current	$P0_0$ to $P0_7$, $P1_0$ to $P1_7$, $P2_0$ to $P2_7$, $P3_0$ to $P3_7$, $P4_0$ to $P4_7$, $P5_0$ to $P5_7$, $P6_0$ to $P6_7$, $P7_0$ to $P7_7$, $P8_0$ to $P8_7$, $P9_0$ to $P9_7$, $P10_0$ to $P10_7$, X_{IN}, $\overline{RESET}$, CNVss, BYTE		V_I=0V				–4.0	µA
R_{PULLUP}	Pull-up resistance	$P0_0$ to $P0_7$, $P1_0$ to $P1_7$, $P2_0$ to $P2_7$, $P3_0$ to $P3_7$, $P4_0$ to $P4_7$, $P5_0$ to $P5_7$, $P6_0$ to $P6_7$, $P7_2$ to $P7_7$, $P8_0$ to $P8_4$, $P8_6$,$P8_7$, $P9_0$ to $P9_7$, $P10_0$ to $P10_7$		V_I=0V		20	75	330	kΩ
R_{fXIN}	Feedback resistance	X_{IN}					3.0		MΩ
R_{fXCIN}	Feedback resistance	X_{CIN}					10.0		MΩ
V_{RAM}	RAM retention voltage			When clock is stopped		2.0			V
I_{CC}	Power supply current	In single-chip mode, the output pins are open and other pins are V_{SS}		Mask ROM version	$f(X_{IN})$=10MHz Square wave, no division		9.5	21.25	mA
				Flash memory 3V version	$f(X_{IN})$=10MHz Square wave, no division		12.0	21.25	mA
				Mask ROM version, flash memory 3V version	$f(X_{CIN})$=32kHz Square wave		45.0		µA
				Flash memory 3V version program	$f(X_{IN})$=10MHz Square wave, division by 2		14.0		mA
				Flash memory 3V version erase	$f(X_{IN})$=10MHz Square wave, division by 2		17.0		mA
				Mask ROM version, flash memory 3V version	$f(X_{CIN})$=32kHz When a WAIT instruction is executed. Oscillation capacity High (Note2)		2.8		µA
					$f(X_{CIN})$=32kHz When a WAIT instruction is executed. Oscillation capacity Low (Note2)		0.9		µA
					When clock is stopped Ta=25°C			1.0	µA
					When clock is stopped Ta=85°C			20.0	

Note 1: Specify a product of -40°C to 85°C to use it.

Note 2: With one timer operated using f_{C32}.

Table 1.26.4. A-D conversion characteristics (referenced to V_{CC} = AV_{CC} = V_{REF} = 2.4V to 3.6V, V_{SS} = AV_{SS} = 0V, at Ta = – 20°C to 85°C / – 40°C to 85°C (Note2), $f(X_{IN})$=10MHz unless otherwise specified)

Symbol	Parameter		Measuring condition	Standard			Unit
				Min.	Typ.	Max	
–	Resolution		V_{REF} =V_{CC}			10	Bits
–	Absolute accuracy	Sample & hold function not available (8 bit)	V_{REF} =V_{CC}=3V, f_{AD}=f_{AD}/2			±2	LSB
R_{LADDER}	Ladder resistance		V_{REF} =V_{CC}	10		40	kΩ
t_{CONV}	Conversion time(8bit)			9.8			µs
V_{REF}	Reference voltage			2.4		V_{CC}	V
V_{IA}	Analog input voltage			0		V_{REF}	V

Note 1: Connect AV_{CC} pin to V_{CC} pin and apply the same electric potential.

Note 2: Specify a product of –40°C to 85°C to use it.

Table 1.26.5. D-A conversion characteristics (referenced to V_{CC} = 2.4V to 3.6V, V_{SS} = AV_{SS} = 0V, V_{REF}=3V, at Ta = – 20°C to 85°C / – 40°C to 85°C (Note2), $f(X_{IN})$=10MHz unless otherwise specified)

Symbol	Parameter	Measuring condition	Standard			Unit
			Min.	Typ.	Max	
–	Resolution				8	Bits
–	Absolute accuracy				1.0	%
t_{su}	Setup time				3	µs
R_O	Output resistance		4	10	20	kΩ
I_{VREF}	Reference power supply input current	(Note1)			1.0	mA

Note 1: This applies when using one D-A converter, with the D-A register for the unused D-A converter set to "00_{16}". The A-D converter's ladder resistance is not included.

Also, when DA register contents are not "00", the current I_{VREF} always flows even though Vref may have been set to be "unconnected" by the A-D control register.

Note 2: Specify a product of –40°C to 85°C to use it.

Table 1.26.6. Flash memory version electrical characteristics (referenced to V_{CC} = 2.7V to 3.6V, at Ta =0°C to 60°C unless otherwise specified)

Parameter	Standard			Unit
	Min.	Typ.	Max	
Page program time		6	120	ms
Block erase time		50	600	ms
Erase all unlocked blocks time		50 X n (Note)	600 X n (Note)	ms
Lock bit program time		6	120	ms

Note : n denotes the number of block erases.

Table 1.26.7. Flash memory version program voltage and read operation voltage characteristics (Ta =0°C to 60°C)

Flash program voltage	Flash read operation voltage
V_{CC}=2.7V to 3.6V	V_{CC}=2.4V to 3.6V
V_{CC}=2.7V to 3.4V	V_{CC}=2.2V to 2.4V

Timing requirements

(referenced to V_{CC} = 3V, V_{SS} = 0V, at Ta = – 20°C to 85°C / – 40°C to 85°C (*) unless otherwise specified)

* : Specify a product of -40°C to 85°C to use it.

Table 1.26.8. External clock input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
t_c	External clock input cycle time	100		ns
$t_{w(H)}$	External clock input HIGH pulse width	40		ns
$t_{w(L)}$	External clock input LOW pulse width	40		ns
t_r	External clock rise time		18	ns
t_f	External clock fall time		18	ns

Table 1.26.9. Memory expansion and microprocessor modes

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{ac1(RD-DB)}$	Data input access time (no wait)		(Note)	ns
$t_{ac2(RD-DB)}$	Data input access time (with wait)		(Note)	ns
$t_{ac3(RD-DB)}$	Data input access time (when accessing multiplex bus area)		(Note)	ns
$t_{su(DB-RD)}$	Data input setup time	80		ns
$t_{su(RDY-BCLK)}$	$\overline{RDY}$ input setup time	60		ns
$t_{su(HOLD-BCLK)}$	$\overline{HOLD}$ input setup time	80		ns
$t_{h(RD-DB)}$	Data input hold time	0		ns
$t_{h(BCLK-RDY)}$	$\overline{RDY}$ input hold time	0		ns
$t_{h(BCLK-HOLD)}$	$\overline{HOLD}$ input hold time	0		ns
$t_{d(BCLK-HLDA)}$	$\overline{HLDA}$ output delay time		100	ns

Note: Calculated according to the BCLK frequency as follows:

$$t_{ac1(RD-DB)} = \frac{10^9}{f(BCLK) \times 2} - 90 \quad [ns]$$

$$t_{ac2(RD-DB)} = \frac{3 \times 10^9}{f(BCLK) \times 2} - 90 \quad [ns]$$

$$t_{ac3(RD-DB)} = \frac{3 \times 10^9}{f(BCLK) \times 2} - 90 \quad [ns]$$

Timing requirements

(referenced to V_{CC} = 3V, V_{SS} = 0V, at Ta = – 20°C to 85°C / – 40°C to 85°C (*) unless otherwise specified)

* : Specify a product of –40°C to 85°C to use it.

Table 1.26.10. Timer A input (counter input in event counter mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TA)}$	TAiIN input cycle time	150		ns
$t_{w(TAH)}$	TAiIN input HIGH pulse width	60		ns
$t_{w(TAL)}$	TAiIN input LOW pulse width	60		ns

Table 1.26.11. Timer A input (gating input in timer mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TA)}$	TAiIN input cycle time	600		ns
$t_{w(TAH)}$	TAiIN input HIGH pulse width	300		ns
$t_{w(TAL)}$	TAiIN input LOW pulse width	300		ns

Table 1.26.12. Timer A input (external trigger input in one-shot timer mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TA)}$	TAiIN input cycle time	300		ns
$t_{w(TAH)}$	TAiIN input HIGH pulse width	150		ns
$t_{w(TAL)}$	TAiIN input LOW pulse width	150		ns

Table 1.26.13. Timer A input (external trigger input in pulse width modulation mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(TAH)}$	TAiIN input HIGH pulse width	150		ns
$t_{w(TAL)}$	TAiIN input LOW pulse width	150		ns

Table 1.26.14. Timer A input (up/down input in event counter mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(UP)}$	TAiOUT input cycle time	3000		ns
$t_{w(UPH)}$	TAiOUT input HIGH pulse width	1500		ns
$t_{w(UPL)}$	TAiOUT input LOW pulse width	1500		ns
$t_{su(UP-TIN)}$	TAiOUT input setup time	600		ns
$t_{h(TIN-UP)}$	TAiOUT input hold time	600		ns

Timing requirements

(referenced to V_{CC} = 3V, V_{SS} = 0V, at Ta = – 20°C to 85°C / – 40°C to 85°C (*) unless otherwise specified)

* : Specify a product of –40°C to 85°C to use it.

Table 1.26.15. Timer B input (counter input in event counter mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN input cycle time (counted on one edge)	150		ns
$t_{w(TBH)}$	TBiIN input HIGH pulse width (counted on one edge)	60		ns
$t_{w(TBL)}$	TBiIN input LOW pulse width (counted on one edge)	60		ns
$t_{c(TB)}$	TBiIN input cycle time (counted on both edges)	300		ns
$t_{w(TBH)}$	TBiIN input HIGH pulse width (counted on both edges)	160		ns
$t_{w(TBL)}$	TBiIN input LOW pulse width (counted on both edges)	160		ns

Table 1.26.16. Timer B input (pulse period measurement mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN input cycle time	600		ns
$t_{w(TBH)}$	TBiIN input HIGH pulse width	300		ns
$t_{w(TBL)}$	TBiIN input LOW pulse width	300		ns

Table 1.26.17. Timer B input (pulse width measurement mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TB)}$	TBiIN input cycle time	600		ns
$t_{w(TBH)}$	TBiIN input HIGH pulse width	300		ns
$t_{w(TBL)}$	TBiIN input LOW pulse width	300		ns

Table 1.26.18. A-D trigger input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(AD)}$	$\overline{ADTRG}$ input cycle time (trigger able minimum)	1500		ns
$t_{w(ADL)}$	$\overline{ADTRG}$ input LOW pulse width	200		ns

Table 1.26.19. Serial I/O

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	300		ns
$t_{w(CKH)}$	CLKi input HIGH pulse width	150		ns
$t_{w(CKL)}$	CLKi input LOW pulse width	150		ns
$t_{d(C-Q)}$	TxDi output delay time		160	ns
$t_{h(C-Q)}$	TxDi hold time	0		ns
$t_{su(D-C)}$	RxDi input setup time	50		ns
$t_{h(C-D)}$	RxDi input hold time	90		ns

Table 1.26.20. External interrupt $\overline{INTi}$ inputs

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(INH)}$	$\overline{INTi}$ input HIGH pulse width	380		ns
$t_{w(INL)}$	$\overline{INTi}$ input LOW pulse width	380		ns

Switching characteristics (referenced to V_{CC} = 3V, V_{SS} = 0V at Ta = – 20°C to 85°C / – 40°C to 85°C (Note 3), CM15 = "1" unless otherwise specified)

Table 1.26.21. Memory expansion and microprocessor modes (with no wait)

Symbol	Parameter	Measuring condition	Standard		Unit
			Min.	Max.	
$t_{d(BCLK-AD)}$	Address output delay time	Figure 1.26.1		60	ns
$t_{h(BCLK-AD)}$	Address output hold time (BCLK standard)		4		ns
$t_{h(RD-AD)}$	Address output hold time (RD standard)		0		ns
$t_{h(WR-AD)}$	Address output hold time (WR standard)		0		ns
$t_{d(BCLK-CS)}$	Chip select output delay time			60	ns
$t_{h(BCLK-CS)}$	Chip select output hold time (BCLK standard)		4		ns
$t_{d(BCLK-ALE)}$	ALE signal output delay time			60	ns
$t_{h(BCLK-ALE)}$	ALE signal output hold time		– 4		ns
$t_{d(BCLK-RD)}$	RD signal output delay time			60	ns
$t_{h(BCLK-RD)}$	RD signal output hold time		0		ns
$t_{d(BCLK-WR)}$	WR signal output delay time			60	ns
$t_{h(BCLK-WR)}$	WR signal output hold time		0		ns
$t_{d(BCLK-DB)}$	Data output delay time (BCLK standard)			80	ns
$t_{h(BCLK-DB)}$	Data output hold time (BCLK standard)		4		ns
$t_{d(DB-WR)}$	Data output delay time (WR standard)		(Note1)		ns
$t_{h(WR-DB)}$	Data output hold time (WR standard)(Note2)		0		ns

Note 1: Calculated according to the BCLK frequency as follows:

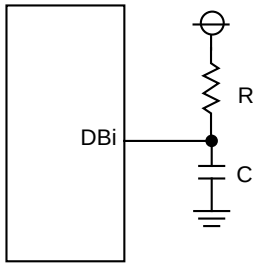
$$td(DB - WR) = \frac{10^9}{f(BCLK) \times 2} - 80 \quad [ns]$$

Note 2: This is standard value shows the timing when the output is off, and doesn't show hold time of data bus.
Hold time of data bus is different by capacitor volume and pull-up (pull-down) resistance value.
Hold time of data bus is expressed in

$$t = -CR \times \ln (1 - V_{OL} / V_{CC})$$

by a circuit of the right figure.
For example, when $V_{OL} = 0.2V_{CC}$, C = 30pF, R = 1kΩ, hold time of output "L" level is

$$t = -30pF \times 1k\Omega \times \ln (1 - 0.2V_{CC} / V_{CC})$$
$$= 6.7ns.$$



Note 3: Specify a product of –40°C to 85°C to use it.

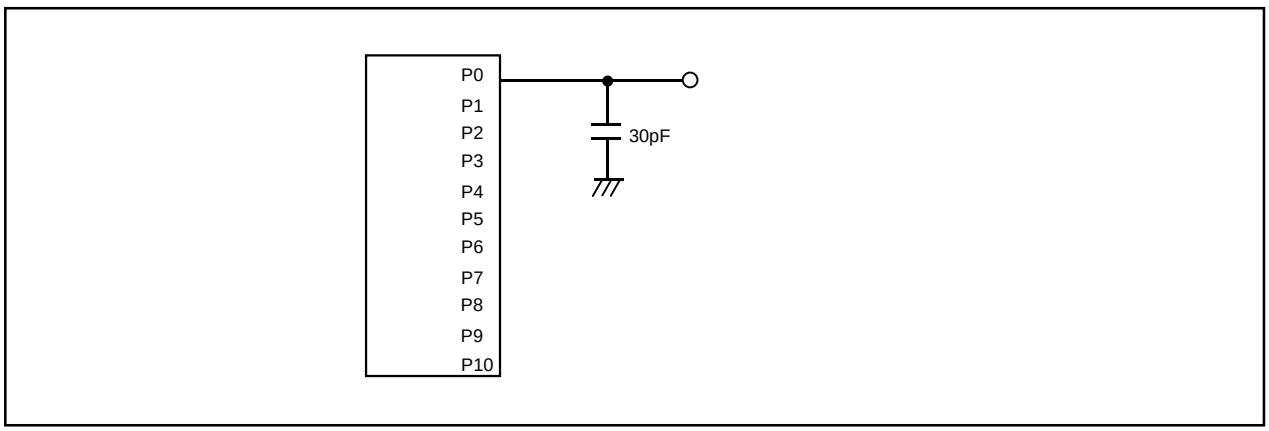


Figure 1.26.1. Port P0 to P10 measurement circuit

Switching characteristics (referenced to V_{CC} = 3V, V_{SS} = 0V at Ta = – 20°C to 85°C / – 40°C to 85°C (Note 3), CM15 = "1" unless otherwise specified)

Table 1.26.22. Memory expansion and microprocessor modes (when accessing external memory area with wait)

Symbol	Parameter	Measuring condition	Standard		Unit
			Min.	Max.	
$t_{d(BCLK-AD)}$	Address output delay time	Figure 1.26.1		60	ns
$t_{h(BCLK-AD)}$	Address output hold time (BCLK standard)		4		ns
$t_{h(RD-AD)}$	Address output hold time (RD standard)		0		ns
$t_{h(WR-AD)}$	Address output hold time (WR standard)		0		ns
$t_{d(BCLK-CS)}$	Chip select output delay time			60	ns
$t_{h(BCLK-CS)}$	Chip select output hold time (BCLK standard)		4		ns
$t_{d(BCLK-ALE)}$	ALE signal output delay time			60	ns
$t_{h(BCLK-ALE)}$	ALE signal output hold time		– 4		ns
$t_{d(BCLK-RD)}$	RD signal output delay time			60	ns
$t_{h(BCLK-RD)}$	RD signal output hold time		0		ns
$t_{d(BCLK-WR)}$	WR signal output delay time			60	ns
$t_{h(BCLK-WR)}$	WR signal output hold time		0		ns
$t_{d(BCLK-DB)}$	Data output delay time (BCLK standard)			80	ns
$t_{h(BCLK-DB)}$	Data output hold time (BCLK standard)		4		ns
$t_{d(DB-WR)}$	Data output delay time (WR standard)		(Note1)		ns
$t_{h(WR-DB)}$	Data output hold time (WR standard)(Note2)		0		ns

Note 1: Calculated according to the BCLK frequency as follows:

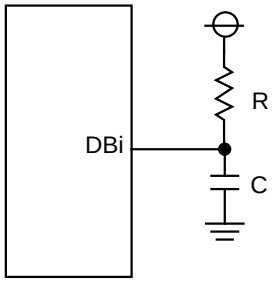
$$td(DB - WR) = \frac{10^9}{f(BCLK)} - 80 \quad [ns]$$

Note 2: This is standard value shows the timing when the output is off, and doesn't show hold time of data bus.
Hold time of data bus is different by capacitor volume and pull-up (pull-down) resistance value.
Hold time of data bus is expressed in

$$t = -CR \times \ln(1 - V_{OL} / V_{CC})$$

by a circuit of the right figure.
For example, when $V_{OL} = 0.2V_{CC}$, C = 30pF, R = 1kΩ, hold time of output "L" level is

$$t = -30pF \times 1k\Omega \times \ln(1 - 0.2V_{CC} / V_{CC})$$
$$= 6.7ns.$$



Note 3: Specify a product of –40°C to 85°C to use it.

Switching characteristics (referenced to V_{CC} = 3V, V_{SS} = 0V at Ta = – 20°C to 85°C / – 40°C to 85°C (Note 2), CM15 = "1" unless otherwise specified)

Table 1.26.23. Memory expansion and microprocessor modes (when accessing external memory area with wait, and select multiplexed bus)

Symbol	Parameter	Measuring condition	Standard		Unit
			Min.	Max.	
$t_{d(BCLK-AD)}$	Address output delay time	Figure 1.26.1		60	ns
$t_{h(BCLK-AD)}$	Address output hold time (BCLK standard)		4		ns
$t_{h(RD-AD)}$	Address output hold time (RD standard)		(Note 1)		ns
$t_{h(WR-AD)}$	Address output hold time (WR standard)		(Note 1)		ns
$t_{d(BCLK-CS)}$	Chip select output delay time			60	ns
$t_{h(BCLK-CS)}$	Chip select output hold time (BCLK standard)		4		ns
$t_{h(RD-CS)}$	Chip select output hold time (RD standard)		(Note 1)		ns
$t_{h(WR-CS)}$	Chip select output hold time (WR standard)		(Note 1)		ns
$t_{d(BCLK-RD)}$	RD signal output delay time			60	ns
$t_{h(BCLK-RD)}$	RD signal output hold time		0		ns
$t_{d(BCLK-WR)}$	WR signal output delay time			60	ns
$t_{h(BCLK-WR)}$	WR signal output hold time		0		ns
$t_{d(BCLK-DB)}$	Data output delay time (BCLK standard)			80	ns
$t_{h(BCLK-DB)}$	Data output hold time (BCLK standard)		4		ns
$t_{d(DB-WR)}$	Data output delay time (WR standard)		(Note 1)		ns
$t_{h(WR-DB)}$	Data output hold time (WR standard)		(Note 1)		ns
$t_{d(BCLK-ALE)}$	ALE signal output delay time (BCLK standard)			60	ns
$t_{h(BCLK-ALE)}$	ALE signal output hold time (BCLK standard)		– 4		ns
$t_{d(AD-ALE)}$	ALE signal output delay time (Address standard)		(Note 1)		ns
$t_{h(ALE-AD)}$	ALE signal output hold time(Address standard)		40		ns
$t_{d(AD-RD)}$	Post-address RD signal output delay time		0		ns
$t_{d(AD-WR)}$	Post-address WR signal output delay time		0		ns
$t_{dZ(RD-AD)}$	Address output floating start time			8	ns

Note 1: Calculated according to the BCLK frequency as follows:

$$th(RD - AD) = \frac{10^9}{f(BCLK) \times 2} \quad [ns]$$

$$th(WR - AD) = \frac{10^9}{f(BCLK) \times 2} \quad [ns]$$

$$th(RD - CS) = \frac{10^9}{f(BCLK) \times 2} \quad [ns]$$

$$th(WR - CS) = \frac{10^9}{f(BCLK) \times 2} \quad [ns]$$

$$td(DB - WR) = \frac{10^9 \times 3}{f(BCLK) \times 2} - 80 \quad [ns]$$

$$th(WR - DB) = \frac{10^9}{f(BCLK) \times 2} \quad [ns]$$

$$td(AD - ALE) = \frac{10^9}{f(BCLK) \times 2} - 45 \quad [ns]$$

Note 2: Specify a product of –40°C to 85°C to use it.

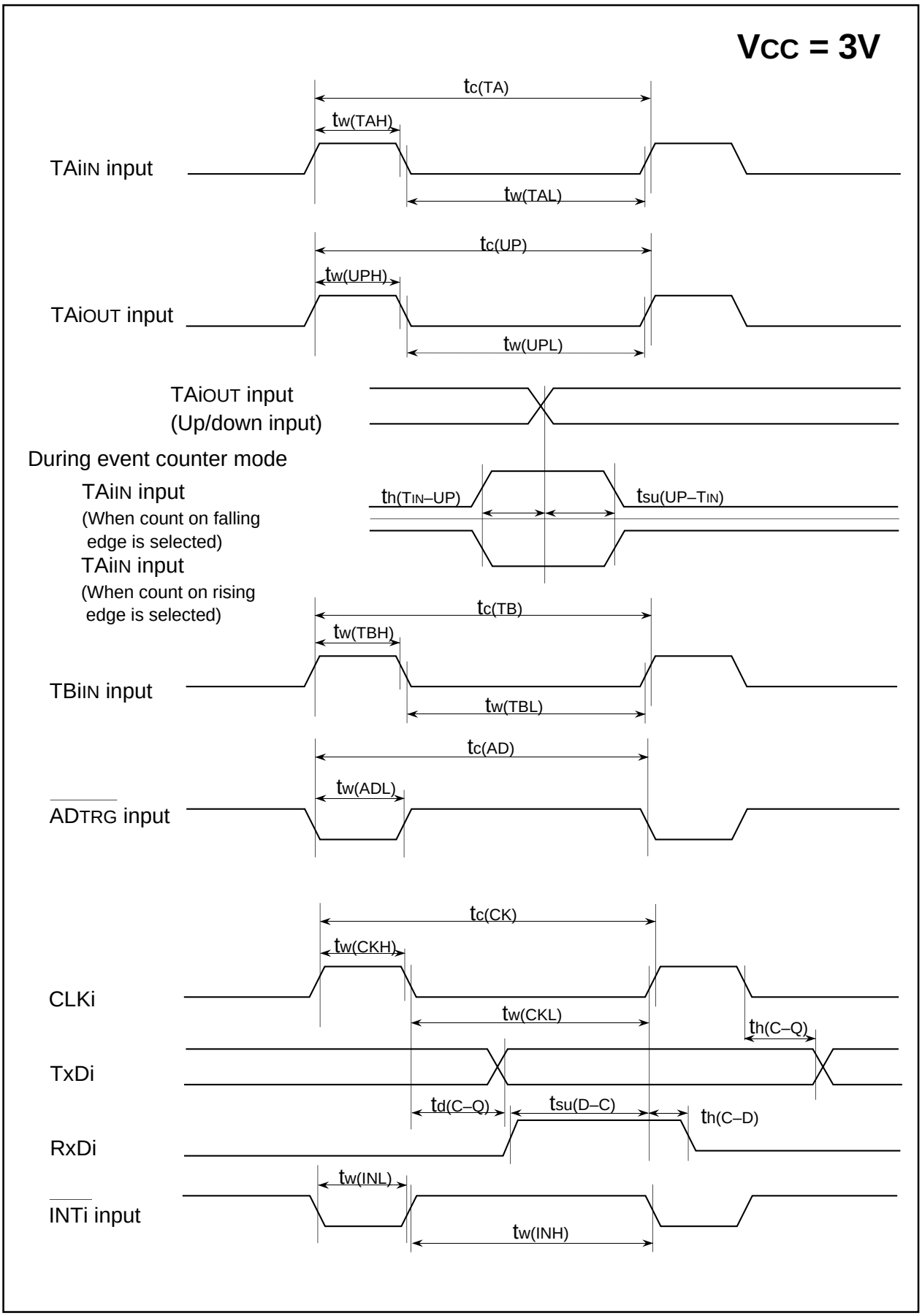
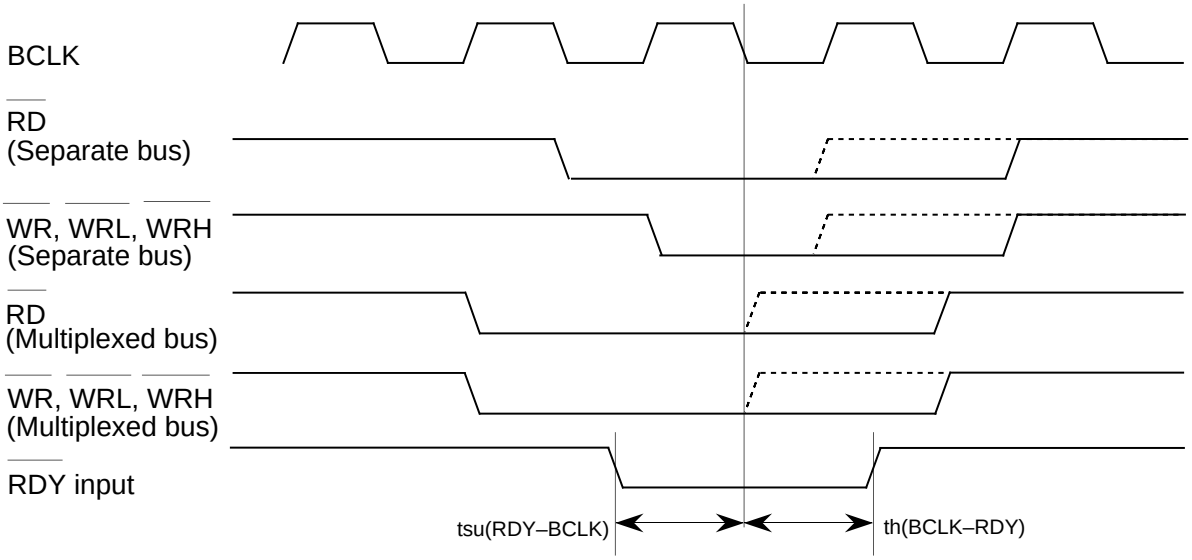


Figure 1.26.2. Vcc=3V timing diagram (1)

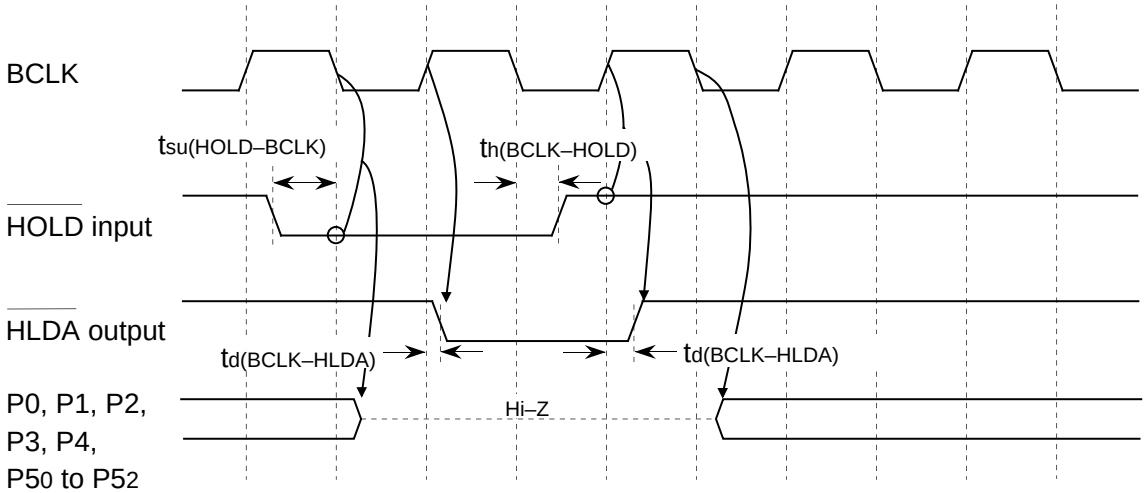
Vcc = 3V

Memory Expansion Mode and Microprocessor Mode

(Valid only with wait)



(Valid with or without wait)



Note: The above pins are set to high-impedance regardless of the input level of the BYTE pin and bit (PM06) of processor mode register 0 selects the function of ports P40 to P43.

Measuring conditions :

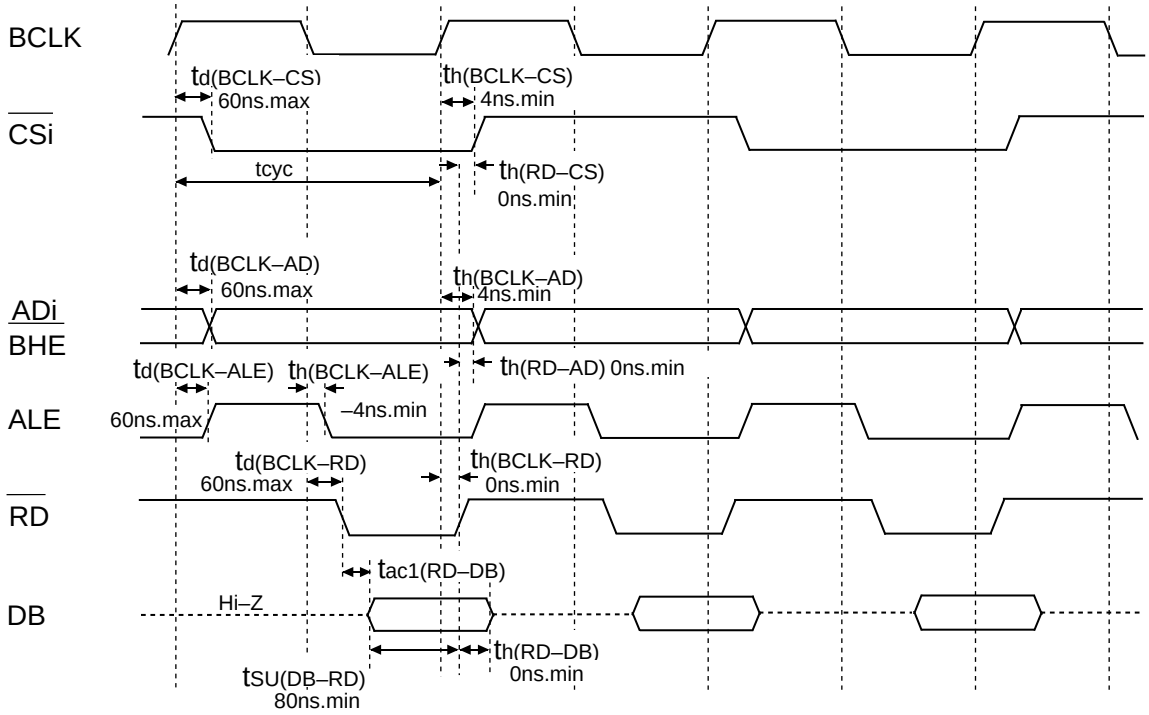
- Vcc=3V
- Input timing voltage : Determined with VIL=0.6V, VIH=2.4V
- Output timing voltage : Determined with VOL=1.5V, VOH=1.5V

Figure 1.26.3. Vcc=3V timing diagram (2)

Vcc = 3V

Memory Expansion Mode and Microprocessor Mode
(With no wait)

Read timing



Write timing

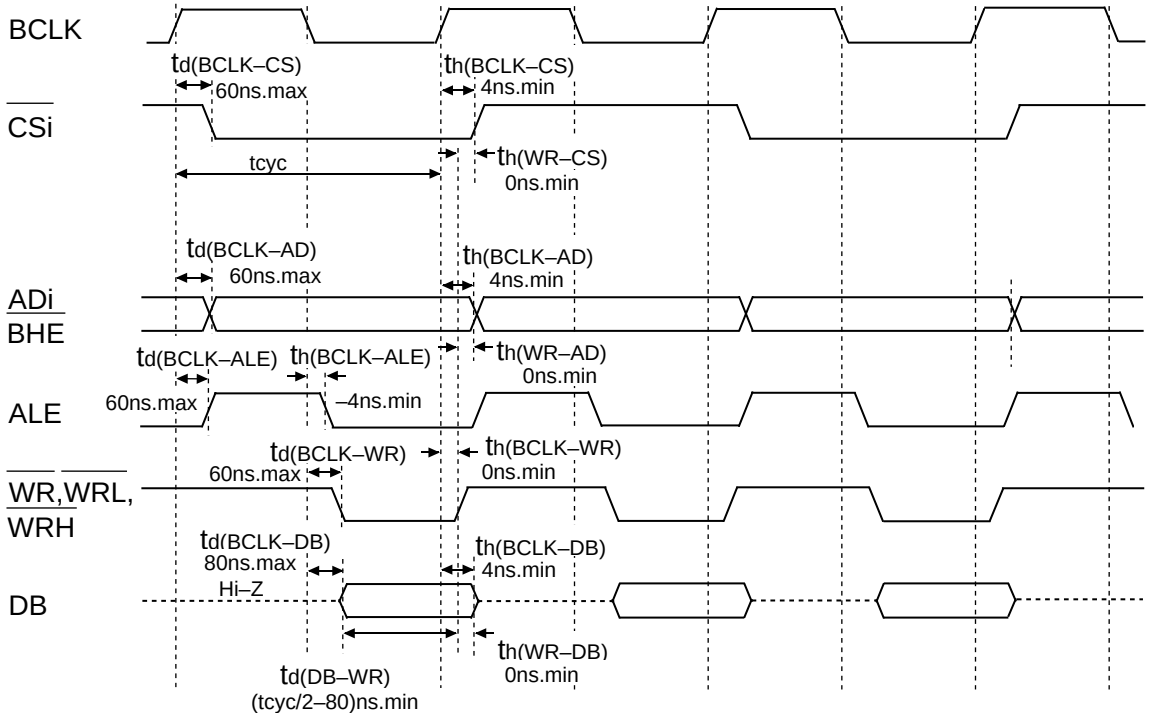


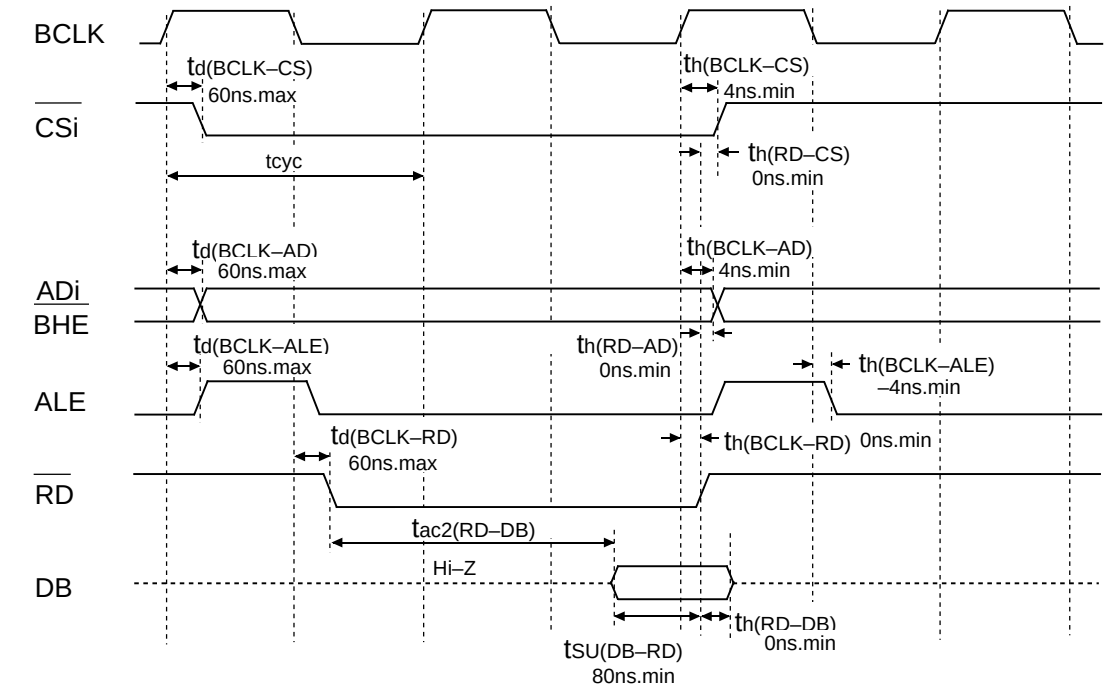
Figure 1.26.4. Vcc=3V timing diagram (3)

Memory Expansion Mode and Microprocessor Mode

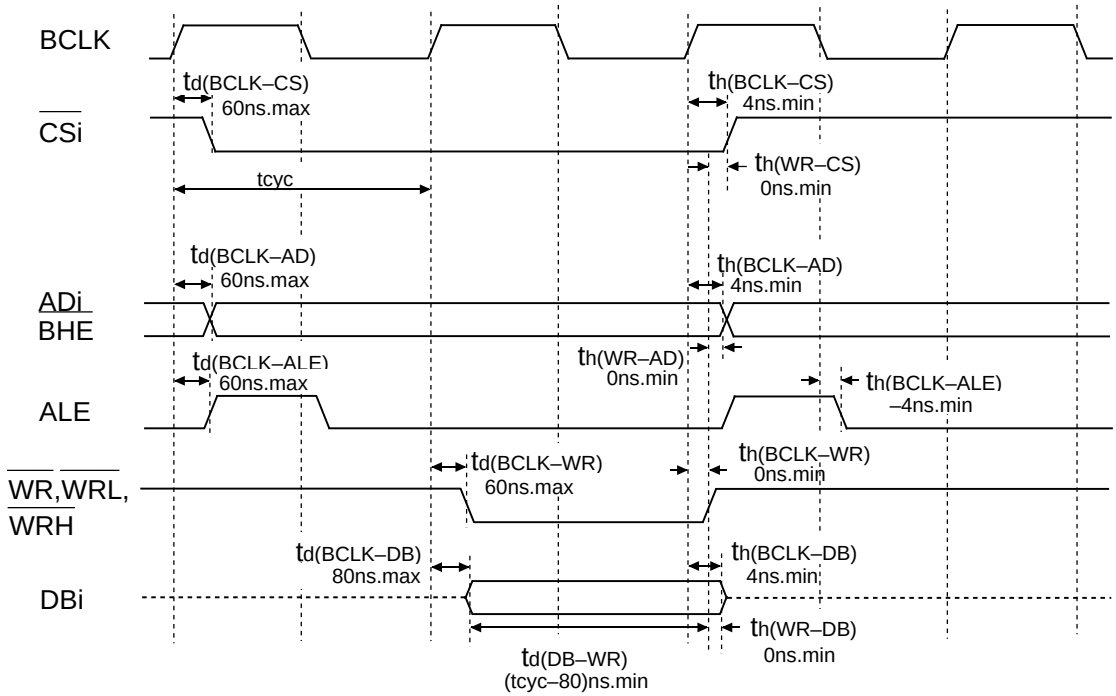
Vcc = 3V

(When accessing external memory area with wait)

Read timing



Write timing



Measuring conditions :

- Vcc=3V
- Input timing voltage : Determined with VIL=0.48V, VIH=1.5V
- Output timing voltage : Determined with VOL=1.5V, VOH=1.5V

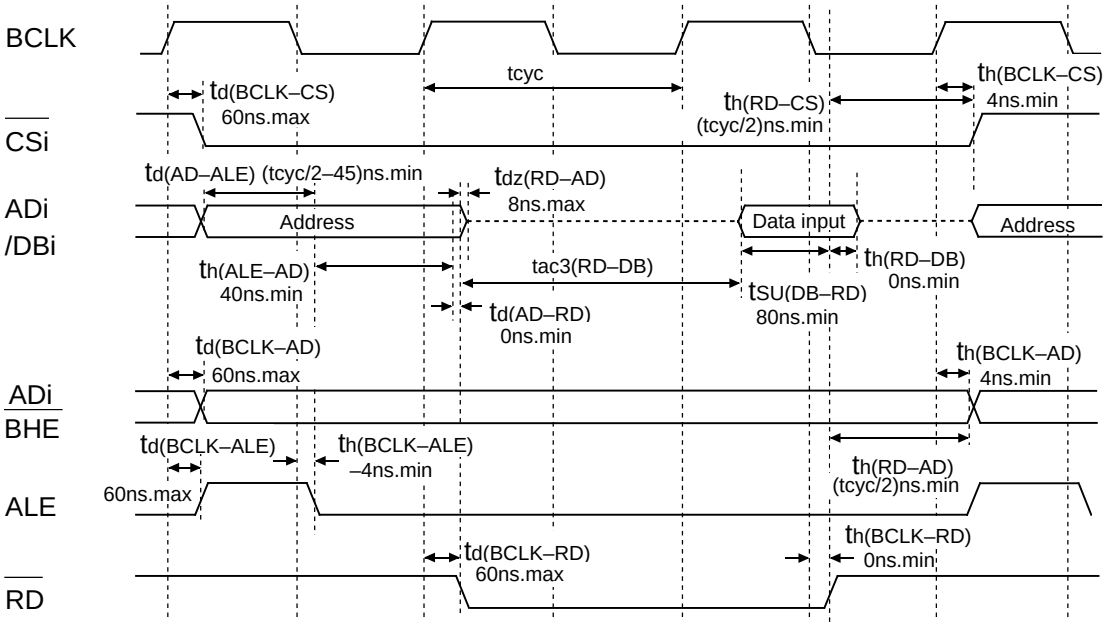
Figure 1.26.5. Vcc=3V timing diagram (4)

Vcc = 3V

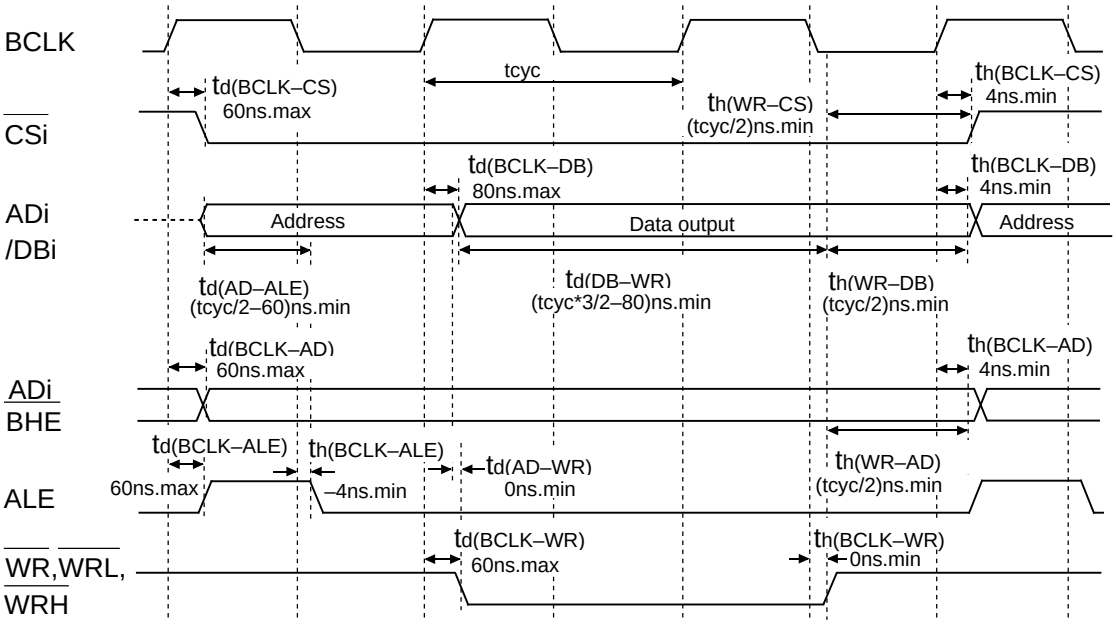
Memory Expansion Mode and Microprocessor Mode

(When accessing external memory area with wait, and select multiplexed bus)

Read timing



Write timing



Measuring conditions :

- Vcc=3V
- Input timing voltage : Determined with VIL=0.48V,VIH=1.5V
- Output timing voltage : Determined with VOL=1.5V,VOH=1.5V

Figure 1.26.6. Vcc=3V timing diagram (5)

Usage Precaution

Timer A (timer mode)

(1) Reading the timer Ai register while a count is in progress allows reading, with arbitrary timing, the value of the counter. Reading the timer Ai register with the reload timing gets "FFFF$_{16}$". Reading the timer Ai register after setting a value in the timer Ai register with a count halted but before the counter starts counting gets a proper value.

Timer A (event counter mode)

(1) Reading the timer Ai register while a count is in progress allows reading, with arbitrary timing, the value of the counter. Reading the timer Ai register with the reload timing gets "FFFF$_{16}$" by underflow or "0000$_{16}$" by overflow. Reading the timer Ai register after setting a value in the timer Ai register with a count halted but before the counter starts counting gets a proper value.

(2) When stop counting in free run type, set timer again.

Timer A (one-shot timer mode)

(1) Setting the count start flag to "0" while a count is in progress causes as follows:
- The counter stops counting and a content of reload register is reloaded.
- The TAi$_{OUT}$ pin outputs "L" level.
- The interrupt request generated and the timer Ai interrupt request bit goes to "1".

(2) The timer Ai interrupt request bit goes to "1" if the timer's operation mode is set using any of the following procedures:
- Selecting one-shot timer mode after reset.
- Changing operation mode from timer mode to one-shot timer mode.
- Changing operation mode from event counter mode to one-shot timer mode.

Therefore, to use timer Ai interrupt (interrupt request bit), set timer Ai interrupt request bit to "0" after the above listed changes have been made.

Timer A (pulse width modulation mode)

(1) The timer Ai interrupt request bit becomes "1" if setting operation mode of the timer in compliance with any of the following procedures:
- Selecting PWM mode after reset.
- Changing operation mode from timer mode to PWM mode.
- Changing operation mode from event counter mode to PWM mode.

Therefore, to use timer Ai interrupt (interrupt request bit), set timer Ai interrupt request bit to "0" after the above listed changes have been made.

(2) Setting the count start flag to "0" while PWM pulses are being output causes the counter to stop counting. If the TAi$_{OUT}$ pin is outputting an "H" level in this instance, the output level goes to "L", and the timer Ai interrupt request bit goes to "1". If the TAi$_{OUT}$ pin is outputting an "L" level in this instance, the level does not change, and the timer Ai interrupt request bit does not becomes "1".

Timer B (timer mode, event counter mode)

(1) Reading the timer Bi register while a count is in progress allows reading , with arbitrary timing, the value of the counter. Reading the timer Bi register with the reload timing gets "FFFF$_{16}$". Reading the timer Bi register after setting a value in the timer Bi register with a count halted but before the counter starts counting gets a proper value.

Timer B (pulse period/pulse width measurement mode)

(1) If changing the measurement mode select bit is set after a count is started, the timer Bi interrupt request bit goes to “1”.

(2) When the first effective edge is input after a count is started, an indeterminate value is transferred to the reload register. At this time, timer Bi interrupt request is not generated.

A-D Converter

(1) Write to each bit (except bit 6) of A-D control register 0, to each bit of A-D control register 1, and to bit 0 of A-D control register 2 when A-D conversion is stopped (before a trigger occurs).
In particular, when the Vref connection bit is changed from “0” to “1”, start A-D conversion after an elapse of 1 μs or longer.

(2) When changing A-D operation mode, select analog input pin again.

(3) Using one-shot mode or single sweep mode
Read the correspondence A-D register after confirming A-D conversion is finished. (It is known by A-D conversion interrupt request bit.)

(4) Using repeat mode, repeat sweep mode 0 or repeat sweep mode 1
Use the undivided main clock as the internal CPU clock.

Stop Mode and Wait Mode

(1) When returning from stop mode by hardware reset, $\overline{\text{RESET}}$ pin must be set to “L” level until main clock oscillation is stabilized.

(2) When switching to either wait mode or stop mode, instructions occupying four bytes either from the WAIT instruction or from the instruction that sets the every-clock stop bit to “1” within the instruction queue are prefetched and then the program stops. So put at least four NOPs in succession either to the WAIT instruction or to the instruction that sets the every-clock stop bit to “1”.

Interrupts

(1) Reading address 00000_{16}

- When maskable interrupt is occurred, CPU read the interrupt information (the interrupt number and interrupt request level) in the interrupt sequence.
  The interrupt request bit of the certain interrupt written in address 00000_{16} will then be set to “0”.
  Reading address 00000_{16} by software sets enabled highest priority interrupt source request bit to “0”.
  Though the interrupt is generated, the interrupt routine may not be executed.
  Do not read address 00000_{16} by software.

(2) Setting the stack pointer

- The value of the stack pointer immediately after reset is initialized to 0000_{16}. Accepting an interrupt before setting a value in the stack pointer may become a factor of runaway. Be sure to set a value in the stack pointer before accepting an interrupt.
  When using the $\overline{\text{NMI}}$ interrupt, initialize the stack point at the beginning of a program. Concerning the first instruction immediately after reset, generating any interrupts including the $\overline{\text{NMI}}$ interrupt is prohibited.

(3) The $\overline{\text{NMI}}$ interrupt

- The $\overline{\text{NMI}}$ interrupt can not be disabled. Be sure to connect $\overline{\text{NMI}}$ pin to Vcc via a pull-up resistor if unused.
- Do not get either into stop mode with the $\overline{\text{NMI}}$ pin set to “L”.

(4) External interrupt

• When the polarity of the $\overline{INT0}$ to $\overline{INT5}$ pins is changed, the interrupt request bit is sometimes set to "1". After changing the polarity, set the interrupt request bit to "0".

(5) Rewrite the interrupt control register

• To rewrite the interrupt control register, do so at a point that does not generate the interrupt request for that register. If there is possibility of the interrupt request occur, rewrite the interrupt control register after the interrupt is disabled. The program examples are described as follow:

Example 1:

```
INT_SWITCH1:
    FCLR    I               ; Disable interrupts.
    AND.B   #00h, 0055h     ; Clear TA0IC int. priority level and int. request bit.
    NOP                     ; Four NOP instructions are required when using HOLD function.
    NOP
    FSET    I               ; Enable interrupts.
```

Example 2:

```
INT_SWITCH2:
    FCLR    I               ; Disable interrupts.
    AND.B   #00h, 0055h     ; Clear TA0IC int. priority level and int. request bit.
    MOV.W   MEM, R0         ; Dummy read.
    FSET    I               ; Enable interrupts.
```

Example 3:

```
INT_SWITCH3:
    PUSHC   FLG             ; Push Flag register onto stack
    FCLR    I               ; Disable interrupts.
    AND.B   #00h, 0055h     ; Clear TA0IC int. priority level and int. request bit.
    POPC    FLG             ; Enable interrupts.
```

The reason why two NOP instructions (four when using the HOLD function) or dummy read are inserted before FSET I in Examples 1 and 2 is to prevent the interrupt enable flag I from being set before the interrupt control register is rewritten due to effects of the instruction queue.

• When a instruction to rewrite the interrupt control register is executed but the interrupt is disabled, the interrupt request bit is not set sometimes even if the interrupt request for that register has been generated. This will depend on the instruction. If this creates problems, use the below instructions to change the register.
Instructions : AND, OR, BCLR, BSET

Noise

(1) Insert bypass capacitor between V_{CC} and V_{SS} pin for noise and latch up countermeasure.

• Insert bypass capacitor (about 0.1 μF) and connect short and wide line between V_{CC} and V_{SS} lines.

Notes on the microprocessor mode and transition after shifting from the microprocessor mode to the memory expansion mode

- Microprocessor mode

  In microprocessor mode, the SFR, internal RAM, and external memory space can be accessed.
  For that reason, the internal ROM area cannot be accessed.

- Memory expansion mode

  In memory expansion mode, external memory can be accessed in addition to the internal memory space (SFR, internal RAM, and internal ROM).

  However, after the reset has been released and the operation of shifting from the microprocessor mode has started ("H" applied to the CNVSS pin), the internal ROM area cannot be accessed even if the CPU shifts to the memory expansion mode.

GZZ-SH13-95B<02A0>

Mask ROM number	

Receipt	Date :	
	Section head signature	Supervisor signature

MITSUBISHI ELECTRIC-CHIP 16-BIT MICROCOMPUTER M30620MCM-XXXFP/GP MASK ROM CONFIRMATION FORM

Note : Please complete all items marked ✵ .

✵	Customer	Company name	TEL ( )	Issuance signature	Submitted by	Supervisor
		Date issued	Date :			

✵1. Check sheet

Mitsubishi processes the mask files generated by the mask file generation utilities out of those held on the floppy disks you give in to us, and forms them into masks. Hence, we assume liability provided that there is any discrepancy between the contents of these mask files and the ROM data to be burned into products we produce. Check thoroughly the contents of the mask files you give in.
Prepare 3.5 inches 2HD (IBM format) floppy disks. And store only one mask file in a floppy disk.

Microcomputer type No. : ☐ M30620MCM-XXXFP ☐ M30620MCM-XXXGP

File code : ☐☐☐☐☐☐☐☐ (hex)

Mask file name : ☐☐☐☐☐☐☐☐ .MSK (alpha-numeric 8-digit)

✵2. Mark specification

The mark specification differs according to the type of package. After entering the mark specification on the separate mark specification sheet (for each package), attach that sheet to this masking check sheet for submission to Mitsubishi.

For the M30620MCM-XXXFP, submit the 100P6S mark specification sheet. For the M30620MCM-XXXGP, submit the 100P6Q mark specification sheet.

✵3. Usage Conditions

For our reference when of testing our products, please reply to the following questions about the usage of the products you ordered.

(1) Which kind of XIN-XOUT oscillation circuit is used?

☐ Ceramic resonator ☐ Quartz-crystal oscillator
☐ External clock input ☐ Other ( )

What frequency do not use?

f(XIN) = ☐ MHz

GZZ-SH13-95B<02A0>

Mask ROM number	

MITSUBISHI ELECTRIC-CHIP 16-BIT MICROCOMPUTER M30620MCM-XXXFP/GP MASK ROM CONFIRMATION FORM

(2) Which kind of XCIN-XCOUT oscillation circuit is used?

☐ Ceramic resonator ☐ Quartz-crystal oscillator

☐ External clock input ☐ Other ( )

What frequency do not use?

f(XCIN) = ☐ kHz

(3) Which operation mode do you use?

☐ Single-chip mode ☐ Memory expansion mode

☐ Microprocessor mode

(4) Which operating supply voltage do you use?

(Circle the operating voltage range of use)

2.2 2.4 2.6 2.7 2.8 2.9 3.0 3.1 3.2 3.3 3.4 3.5 3.6 3.7 3.8 (V)

(5) Which operating ambient temperature do you use?

(Circle the operating temperature range of use)

-50 -40 -30 -20 -10 0 10 20 30 40 50 60 70 80 90 (°C)

(6) Do you use I^2C (Inter IC) bus function?

☐ Not use ☐ Use

(7) Do you use IE (Inter Equipment) bus function?

☐ Not use ☐ Use

Thank you cooperation.

❋4. Special item (Indicate none if there is not specified item)

GZZ-SH13-48B<98A1>

Mask ROM number	

Receipt	Date :	
	Section head signature	Supervisor signature

MITSUBISHI ELECTRIC-CHIP 16-BIT MICROCOMPUTER M30624MGM-XXXFP/GP MASK ROM CONFIRMATION FORM

Note : Please complete all items marked ✵ .

					Issuance signature	Submitted by	Supervisor
✵	Customer	Company name	TEL ( )				
		Date issued	Date :				

✵1. Check sheet

Mitsubishi processes the mask files generated by the mask file generation utilities out of those held on the floppy disks you give in to us, and forms them into masks. Hence, we assume liability provided that there is any discrepancy between the contents of these mask files and the ROM data to be burned into products we produce. Check thoroughly the contents of the mask files you give in.
Prepare 3.5 inches 2HD (IBM format) floppy disks. And store only one mask file in a floppy disk.

Microcomputer type No. : ☐ M30624MGM-XXXFP ☐ M30624MGM-XXXGP

File code : ☐☐☐☐☐☐☐☐ (hex)

Mask file name : ☐☐☐☐☐☐☐☐ .MSK (alpha-numeric 8-digit)

✵2. Mark specification

The mark specification differs according to the type of package. After entering the mark specification on the separate mark specification sheet (for each package), attach that sheet to this masking check sheet for submission to Mitsubishi.

For the M30624MGM-XXXFP, submit the 100P6S mark specification sheet. For the M30624MGM-XXXGP, submit the 100P6Q mark specification sheet.

✵3. Usage Conditions

For our reference when of testing our products, please reply to the following questions about the usage of the products you ordered.

(1) Which kind of XIN-XOUT oscillation circuit is used?

☐ Ceramic resonator ☐ Quartz-crystal oscillator
☐ External clock input ☐ Other ( )

What frequency do not use?

f(XIN) = ☐ MHz

GZZ-SH13-48B<98A1>

Mask ROM number	

MITSUBISHI ELECTRIC-CHIP 16-BIT MICROCOMPUTER M30624MGM-XXXFP/GP MASK ROM CONFIRMATION FORM

(2) Which kind of XCIN-XCOUT oscillation circuit is used?

☐ Ceramic resonator ☐ Quartz-crystal oscillator

☐ External clock input ☐ Other ( )

What frequency do not use?

f(XCIN) = ☐ kHz

(3) Which operation mode do you use?

☐ Single-chip mode ☐ Memory expansion mode

☐ Microprocessor mode

(4) Which operating supply voltage do you use?

(Circle the operating voltage range of use)

2.2 2.4 2.6 2.7 2.8 2.9 3.0 3.1 3.2 3.3 3.4 3.5 3.6 3.7 3.8 (V)

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-50 -40 -30 -20 -10 0 10 20 30 40 50 60 70 80 90 (°C)

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☐ Not use ☐ Use

(7) Do you use IE (Inter Equipment) bus function?

☐ Not use ☐ Use

Thank you cooperation.

❋4. Special item (Indicate none if there is not specified item)

Differences between M16C/62M (Low voltage version) and M30624FGLFP/GP

Item	M16C/62M (Low voltage version)	M30624FGLFP/GP
Memory area	1 Mbyte fixed	Memory expansion 1.2 Mbytes mode 4 Mbytes mode
Serial I/O	No CTS/RTS separate function	CTS/RTS separate function
IIC bus mode	Analog or digital delay is selected as SDA delay	Only analog delay is selected as SDA delay
Memory version	Mask ROM version Flash memory version	Flash memory version only
Standard serial I/O mode (Flash memory version)	Clock synchronized Clock asynchronized	Clock synchronized only

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MITSUBISHI SEMICONDUCTORS
M16C/62M Group (Low voltage version)
Specifications REV.B

Jun. First Edition 2000

Edition by
Committee of editing of Mitsubishi Semiconductor

Published by
Mitsubishi Electric Corp., Kitaitami Works